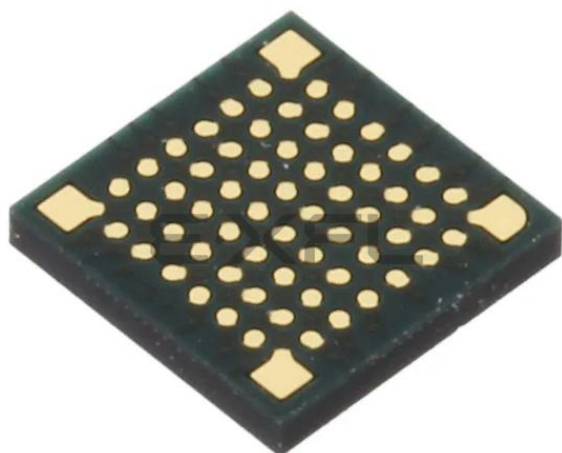




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Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-WFLGA
Supplier Device Package	64-FLGA (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104llala-u0

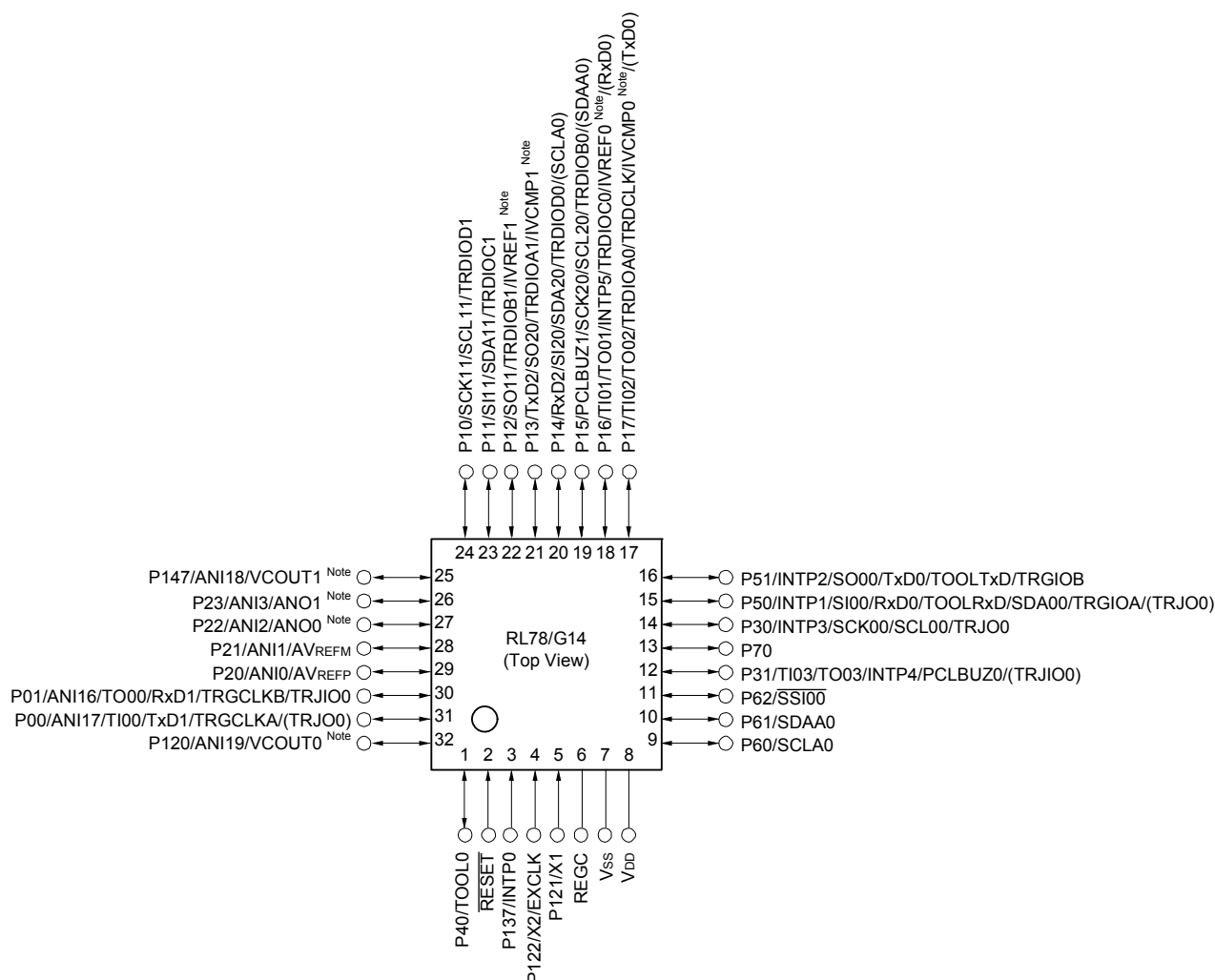
(5/5)

Pin count	Package	Fields of Application Note	Ordering Part Number
80 pins	80-pin plastic LQFP (12 × 12 mm, 0.5 mm pitch)	A	R5F104MFAFB#V0, R5F104MGAFB#V0, R5F104MHAFA#V0, R5F104MJAFB#V0 R5F104MFAFB#X0, R5F104MGAFB#X0, R5F104MHAFA#X0, R5F104MJAFB#X0 R5F104MKAFB#30, R5F104MLAFB#30 R5F104MKAFB#50, R5F104MLAFB#50
		D	R5F104MFDFA#V0, R5F104MGDFA#V0, R5F104MHDFA#V0, R5F104MJDFB#V0 R5F104MFDFA#X0, R5F104MGDFA#X0, R5F104MHDFA#X0, R5F104MJDFB#X0
		G	R5F104MFGFB#V0, R5F104MGGFB#V0, R5F104MHGFB#V0, R5F104MJGFB#V0 R5F104MFGFB#X0, R5F104MGGFB#X0, R5F104MHGFB#X0, R5F104MJGFB#X0 R5F104MKGFB#30, R5F104MLGFB#30 R5F104MKGFB#50, R5F104MLGFB#50
	80-pin plastic LQFP (14 × 14 mm, 0.65 mm pitch)	A	R5F104MFAFA#V0, R5F104MGFAFA#V0, R5F104MHAFA#V0, R5F104MJFAFA#V0 R5F104MFAFA#X0, R5F104MGFAFA#X0, R5F104MHAFA#X0, R5F104MJFAFA#X0 R5F104MKFAFA#30, R5F104MLFAFA#30 R5F104MKFAFA#50, R5F104MLFAFA#50
		D	R5F104MFDFA#V0, R5F104MGDFA#V0, R5F104MHDFA#V0, R5F104MJDFB#V0 R5F104MFDFA#X0, R5F104MGDFA#X0, R5F104MHDFA#X0, R5F104MJDFB#X0
		G	R5F104MFGFA#V0, R5F104MGGFA#V0, R5F104MHGFA#V0, R5F104MJGFA#V0 R5F104MFGFA#X0, R5F104MGGFA#X0, R5F104MHGFA#X0, R5F104MJGFA#X0 R5F104MKGFA#30, R5F104MLGFA#30 R5F104MKGFA#50, R5F104MLGFA#50
100 pins	100-pin plastic LQFP (14 × 14 mm, 0.5 mm pitch)	A	R5F104PFAFB#V0, R5F104PGAFA#V0, R5F104PHAFA#V0, R5F104PJAFB#V0 R5F104PFAFB#X0, R5F104PGAFA#X0, R5F104PHAFA#X0, R5F104PJAFB#X0 R5F104PKAFB#30, R5F104PLAFB#30 R5F104PKAFB#50, R5F104PLAFB#50
		D	R5F104PFDFA#V0, R5F104PGDFA#V0, R5F104PHDFA#V0, R5F104PJDFB#V0 R5F104PFDFA#X0, R5F104PGDFA#X0, R5F104PHDFA#X0, R5F104PJDFB#X0
		G	R5F104PFGFB#V0, R5F104PGGFB#V0, R5F104PHGFB#V0, R5F104PJGFB#V0 R5F104PFGFB#X0, R5F104PGGFB#X0, R5F104PHGFB#X0, R5F104PJGFB#X0 R5F104PKGFB#30, R5F104PLGFB#30 R5F104PKGFB#50, R5F104PLGFB#50
	100-pin plastic LQFP (14 × 20 mm, 0.65 mm pitch)	A	R5F104PFAFA#V0, R5F104PGAFA#V0, R5F104PHAFA#V0, R5F104PJFAFA#V0 R5F104PFAFA#X0, R5F104PGAFA#X0, R5F104PHAFA#X0, R5F104PJFAFA#X0 R5F104PKFAFA#30, R5F104PLFAFA#30 R5F104PKFAFA#50, R5F104PLFAFA#50
		D	R5F104PFDFA#V0, R5F104PGDFA#V0, R5F104PHDFA#V0, R5F104PJDFB#V0 R5F104PFDFA#X0, R5F104PGDFA#X0, R5F104PHDFA#X0, R5F104PJDFB#X0
		G	R5F104PFGFA#V0, R5F104PGGFA#V0, R5F104PHGFA#V0, R5F104PJGFA#V0 R5F104PFGFA#X0, R5F104PGGFA#X0, R5F104PHGFA#X0, R5F104PJGFA#X0 R5F104PKGFA#30, R5F104PLGFA#30 R5F104PKGFA#50, R5F104PLGFA#50

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

- 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)



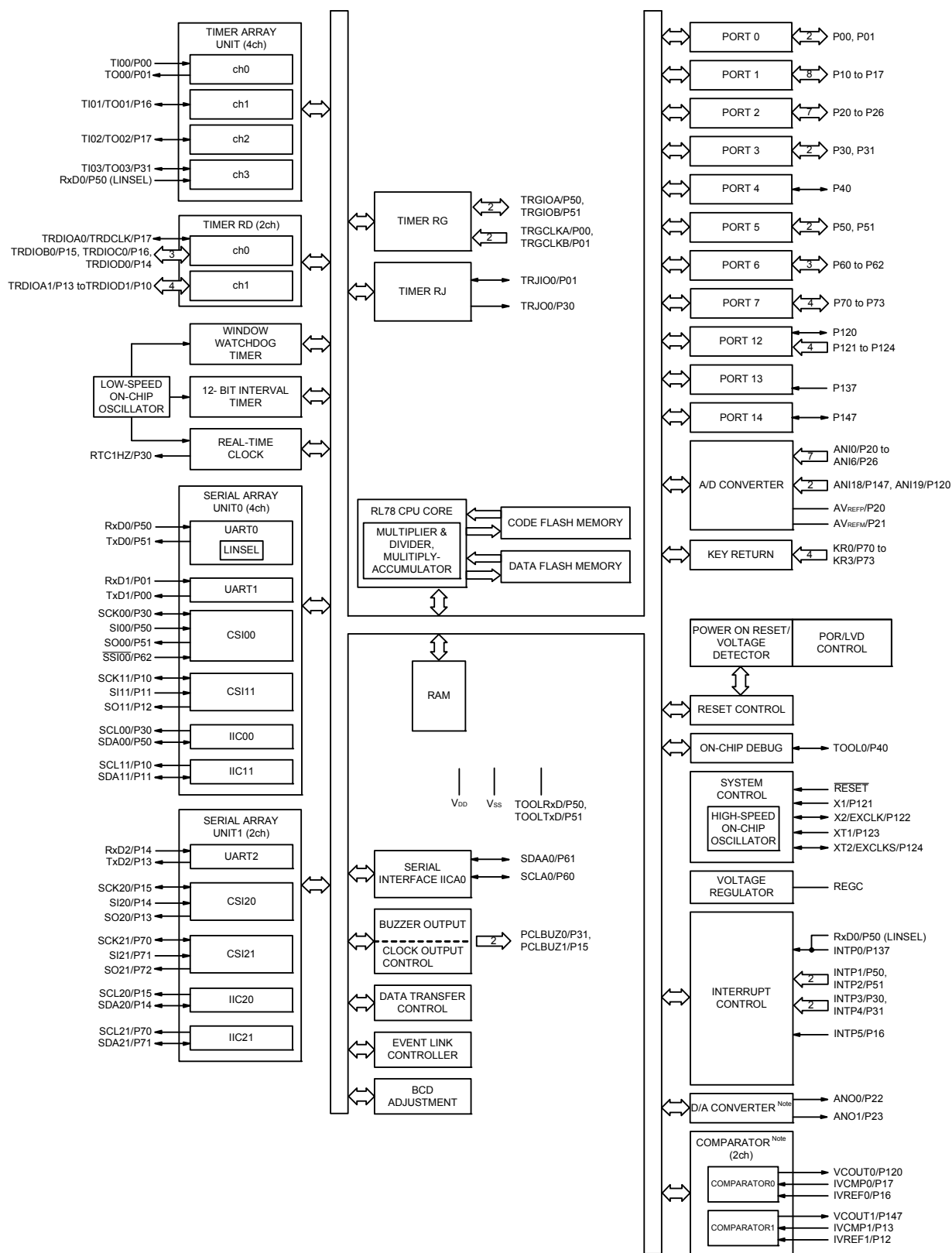
Note Mounted on the 96 KB or more code flash memory products.

Caution Connect the REGC pin to V_{SS} pin via a capacitor (0.47 to 1 μ F).

Remark 1. For pin identification, see 1.4 Pin Identification.

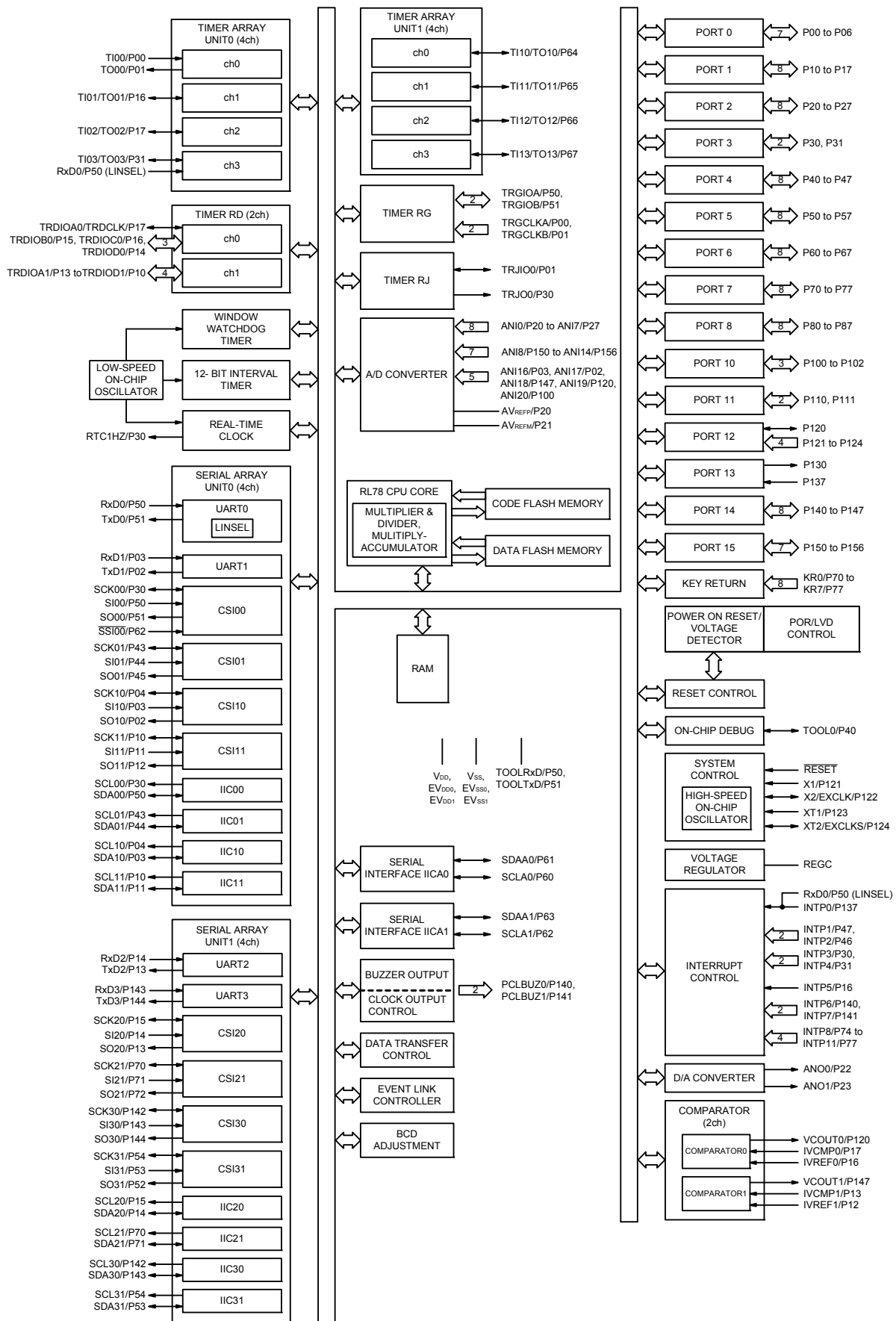
Remark 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

1.5.4 40-pin products



Note Mounted on the 96 KB or more code flash memory products.

1.5.10 100-pin products



1.6 Outline of Functions

[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 16 KB to 64 KB)]

Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

(1/2)

Item		30-pin	32-pin	36-pin	40-pin
		R5F104Ax (x = A, C to E)	R5F104Bx (x = A, C to E)	R5F104Cx (x = A, C to E)	R5F104Ex (x = A, C to E)
Code flash memory (KB)		16 to 64	16 to 64	16 to 64	16 to 64
Data flash memory (KB)		4	4	4	4
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note	2.5 to 5.5 Note
Address space		1 MB			
Main system clock	High-speed system clock	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (high-speed main) mode: 1 to 20 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)			
	High-speed on-chip oscillator clock (f _{IH})	HS (high-speed main) mode: 1 to 32 MHz ($V_{DD} = 2.7$ to 5.5 V), HS (high-speed main) mode: 1 to 16 MHz ($V_{DD} = 2.4$ to 5.5 V), LS (low-speed main) mode: 1 to 8 MHz ($V_{DD} = 1.8$ to 5.5 V), LV (low-voltage main) mode: 1 to 4 MHz ($V_{DD} = 1.6$ to 5.5 V)			
Subsystem clock		—			XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz
Low-speed on-chip oscillator clock		15 kHz (TYP.): $V_{DD} = 1.6$ to 5.5 V			
General-purpose register		8 bits × 32 registers (8 bits × 8 registers × 4 banks)			
Minimum instruction execution time		0.03125 μs (High-speed on-chip oscillator clock: f _{IH} = 32 MHz operation)			
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)			
		—			30.5 μs (Subsystem clock: f _{SUB} = 32.768 kHz operation)
Instruction set		• Data transfer (8/16 bits) • Adder and subtractor/logical operation (8/16 bits) • Multiplication (8 bits × 8 bits, 16 bits × 16 bits), Division (16 bits ÷ 16 bits, 32 bits ÷ 32 bits) • Multiplication and Accumulation (16 bits × 16 bits + 32 bits) • Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc.			
I/O port	Total	26	28	32	36
	CMOS I/O	21	22	26	28
	CMOS input	3	3	3	5
	CMOS output	—	—	—	—
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer RJ: 1 channel, Timer RD: 2 channels, Timer RG: 1 channel)			
	Watchdog timer	1 channel			
	Real-time clock (RTC)	1 channel			
	12-bit interval timer	1 channel			
	Timer output	Timer outputs: 13 channels PWM outputs: 9 channels			
	RTC output	—			1 • 1 Hz (subsystem clock: f _{SUB} = 32.768 kHz)

(Note is listed on the next page.)

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 characteristics

(TA = -40 to +85°C, 1.6 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator	2.7 V ≤ VDD ≤ 5.5 V	1.0		20.0	MHz
		2.4 V ≤ VDD < 2.7 V	1.0		16.0	
		1.8 V ≤ VDD < 2.4 V	1.0		8.0	
		1.6 V ≤ VDD < 1.8 V	1.0		4.0	
XT1 clock oscillation frequency (fxT) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to **AC Characteristics** for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator** in the RL78/G14 User's Manual.

2.2.2 On-chip oscillator characteristics

(TA = -40 to +85°C, 1.6 V ≤ VDD ≤ 5.5 V, VSS = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	f _{IH}			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		-20 to +85°C	1.8 V ≤ VDD ≤ 5.5 V	-1.0		+1.0	%
			1.6 V ≤ VDD < 1.8 V	-5.0		+5.0	%
		-40 to -20°C	1.8 V ≤ VDD ≤ 5.5 V	-1.5		+1.5	%
			1.6 V ≤ VDD < 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	f _{IL}				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to **AC Characteristics** for instruction execution time.

- Note 1.** Total current flowing into V_{DD} and EV_{DD0}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0} or V_{SS}, EV_{SS0}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2.** During HALT instruction execution by flash memory.
- Note 3.** When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 4.** When high-speed system clock and subsystem clock are stopped.
- Note 5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 6.** Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- Note 7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
- | | |
|-----------------------------|---|
| HS (high-speed main) mode: | 2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 32 MHz |
| | 2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz |
| LS (low-speed main) mode: | 1.8 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 8 MHz |
| LV (low-voltage main) mode: | 1.6 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 4 MHz |
- Note 8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remark 1.** f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2.** f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3.** f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4.** f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is T_A = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

(TA = -40 to +85°C, 1.6 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

Parameter	Symbol	Conditions				MIN.	TYP.	MAX.	Unit			
Supply current Note 1	IDD2 Note 2	HALT mode Note 7	HS (high-speed main) mode Note 7	fHOCO = 64 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.79	3.32	mA			
					VDD = 3.0 V		0.79	3.32				
				fHOCO = 32 MHz, fIH = 32 MHz Note 4	VDD = 5.0 V		0.49	2.63				
					VDD = 3.0 V		0.49	2.63				
				fHOCO = 48 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.62	2.57				
					VDD = 3.0 V		0.62	2.57				
				fHOCO = 24 MHz, fIH = 24 MHz Note 4	VDD = 5.0 V		0.4	2.00				
					VDD = 3.0 V		0.4	2.00				
				fHOCO = 16 MHz, fIH = 16 MHz Note 4	VDD = 5.0 V		0.38	1.49				
					VDD = 3.0 V		0.38	1.49				
			LS (low-speed main) mode Note 7	fHOCO = 8 MHz, fIH = 8 MHz Note 4	VDD = 3.0 V		250	800	μA			
					VDD = 2.0 V		250	800				
			LV (low-voltage main) mode Note 7	fHOCO = 4 MHz, fIH = 4 MHz Note 4	VDD = 3.0 V		420	755	μA			
					VDD = 2.0 V		420	755				
			HS (high-speed main) mode Note 7	fMX = 20 MHz Note 3, VDD = 5.0 V	Square wave input		0.30	1.63	mA			
						Resonator connection		0.40		1.85		
					Square wave input		0.30	1.63				
						Resonator connection		0.40		1.85		
					fMX = 10 MHz Note 3, VDD = 5.0 V	Square wave input		0.20		0.89		
							Resonator connection			0.25	0.97	
					fMX = 10 MHz Note 3, VDD = 3.0 V	Square wave input		0.20		0.89		
							Resonator connection			0.25	0.97	
					LS (low-speed main) mode Note 7	fMX = 8 MHz Note 3, VDD = 3.0 V	Square wave input			110	580	μA
							Resonator connection			140	630	
						fMX = 8 MHz Note 3, VDD = 2.0 V	Square wave input			110	580	
							Resonator connection			140	630	
					Subsystem clock oper- ation	fSUB = 32.768 kHz Note 5, TA = -40°C	Square wave input			0.28	0.66	μA
							Resonator connection			0.47	0.85	
			fSUB = 32.768 kHz Note 5, TA = +25°C	Square wave input			0.34	0.66				
				Resonator connection			0.53	0.85				
			fSUB = 32.768 kHz Note 5, TA = +50°C	Square wave input			0.37	2.35				
				Resonator connection			0.56	2.54				
			fSUB = 32.768 kHz Note 5, TA = +70°C	Square wave input			0.61	4.08				
				Resonator connection			0.80	4.27				
			fSUB = 32.768 kHz Note 5, TA = +85°C	Square wave input			1.55	8.09				
				Resonator connection			1.74	8.28				
IDD3 Note 6	STOP mode Note 8	TA = -40°C					0.19	0.57	μA			
		TA = +25°C					0.25	0.57				
		TA = +50°C					0.33	2.26				
		TA = +70°C					0.52	3.99				
		TA = +85°C					1.46	8.00				

(Notes and Remarks are listed on the next page.)

- Note 5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{WDT} when the watchdog timer is in operation.
- Note 6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{ADC} when the A/D converter operates in an operation mode or the HALT mode.
- Note 7.** Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2} or I_{DD3} and I_{LVD} when the LVD circuit is in operation.
- Note 8.** Current flowing during programming of the data flash.
- Note 9.** Current flowing during self-programming.
- Note 10.** For shift time to the SNOOZE mode, see **23.3.3 SNOOZE mode** in the RL78/G14 User's Manual.
- Note 11.** Current flowing only to the D/A converter. The supply current of the RL78 microcontrollers is the sum of I_{DD1} or I_{DD2} and I_{DAC} when the D/A converter operates in an operation mode or the HALT mode.
- Note 12.** Current flowing only to the comparator circuit. The supply current of the RL78 microcontrollers is the sum of I_{DD1}, I_{DD2}, or I_{DD3} and I_{CMP} when the comparator circuit is in operation.
- Note 13.** A comparator and D/A converter are provided in products with 96 KB or more code flash memory.

Remark 1. f_{IL}: Low-speed on-chip oscillator clock frequency

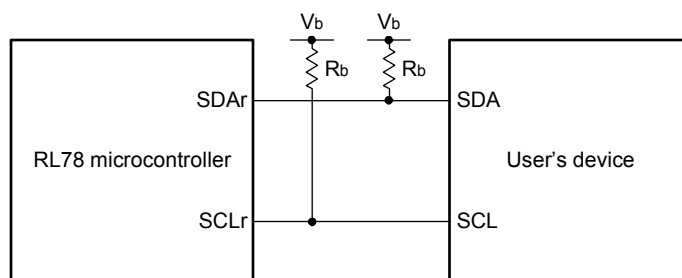
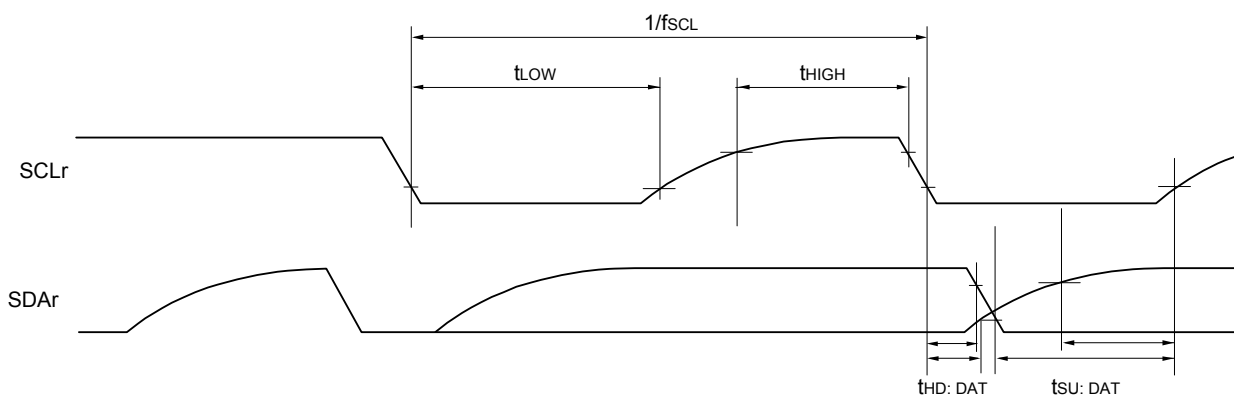
Remark 2. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 3. f_{CLK}: CPU/peripheral hardware clock frequency

Remark 4. Temperature condition of the TYP. value is T_A = 25°C

Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 3 to 5, 14)

Remark 2. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
n: Channel number (mn = 00 to 03, 10 to 13))

Simplified I²C mode connection diagram (during communication at different potential)**Simplified I²C mode serial transfer timing (during communication at different potential)**

Remark 1. $R_b[\Omega]$: Communication line (SDAr, SCLr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance, $V_b[V]$: Communication line voltage

Remark 2. r : IIC number ($r = 00, 01, 10, 11, 20, 30, 31$), g : PIM, POM number ($g = 0, 1, 3$ to $5, 14$)

Remark 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKS mn bit of serial mode register mn (SMR mn). m : Unit number ($m = 0, 1$),
 n : Channel number ($n = 0, 2$), $mn = 00, 01, 02, 10, 12, 13$)

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Input channel	Reference Voltage	Reference voltage (+) = AV _{REFP} Reference voltage (-) = AV _{REFM}	Reference voltage (+) = V _{DD} Reference voltage (-) = V _{SS}	Reference voltage (+) = V _{BGR} Reference voltage (-) = AV _{REFM}
ANI0 to ANI14		Refer to 2.6.1 (1).	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI20		Refer to 2.6.1 (2).		
Internal reference voltage Temperature sensor output voltage		Refer to 2.6.1 (1).		—

(1) When reference voltage (+) = AV_{REFP}/ANI0 (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AV_{REFM}/ANI1 (ADREFM = 1), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V ≤ AV_{REFP} ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V, Reference voltage (+) = AV_{REFP}, Reference voltage (-) = AV_{REFM} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error Note 1	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3	1.8 V ≤ AV _{REFP} ≤ 5.5 V	1.2	±3.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4	1.2	±7.0	LSB
Conversion time	t _{CONV}	10-bit resolution Target pin: ANI2 to ANI14	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875	39	μs
			1.8 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
			1.6 V ≤ V _{DD} ≤ 5.5 V	57	95	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	3.6 V ≤ V _{DD} ≤ 5.5 V	2.375	39	μs
			2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625	39	μs
			2.4 V ≤ V _{DD} ≤ 5.5 V	17	39	μs
Zero-scale error Notes 1, 2	E _{ZS}	10-bit resolution AV _{REFP} = V _{DD} Note 3	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4		±0.50	%FSR
Full-scale error Notes 1, 2	E _{FS}	10-bit resolution AV _{REFP} = V _{DD} Note 3	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±0.25	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4		±0.50	%FSR
Integral linearity error Note 1	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±2.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4		±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3	1.8 V ≤ AV _{REFP} ≤ 5.5 V		±1.5	LSB
			1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4		±2.0	LSB
Analog input voltage	V _{AIN}	ANI2 to ANI14	0		AV _{REFP}	V
		Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 5	V
		Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{TMPS25} Note 5	V

Note 1. Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add ±0.05%FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Note 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).

Note 5. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(3/5)

Items	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input voltage, high	VIH1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0.8 EVDD0	EVDD0	V
		P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	2.2	EVDD0	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0	EVDD0	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	1.5	EVDD0	V
	VIH3	P20 to P27, P150 to P156	0.7 VDD		VDD	V
	VIH4	P60 to P63	0.7 EVDD0		6.0	V
	VIH5	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$	0.8 VDD		VDD	V
Input voltage, low	VIL1	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P140 to P147	Normal input buffer	0	0.2 EVDD0	V
		P01, P03, P04, P10, P14 to P17, P30, P43, P44, P50, P53 to P55, P80, P81, P142, P143	TTL input buffer 4.0 V ≤ EVDD0 ≤ 5.5 V	0	0.8	V
			TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	0	0.5	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	0	0.32	V
	VIL3	P20 to P27, P150 to P156	0		0.3 VDD	V
	VIL4	P60 to P63	0		0.3 EVDD0	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS, $\overline{\text{RESET}}$	0		0.2 VDD	V

Caution The maximum value of VIH of pins P00, P02 to P04, P10, P11, P13 to P15, P17, P30, P43 to P45, P50 to P55, P71, P74, P80 to P82, and P142 to P144 is EVDD0, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

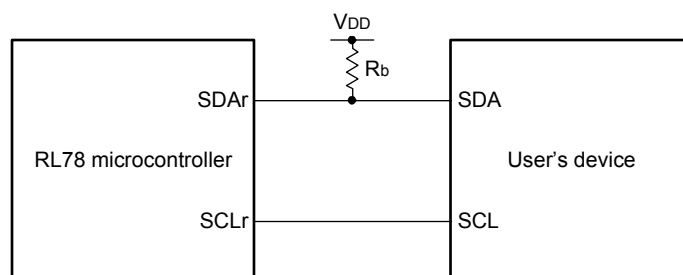
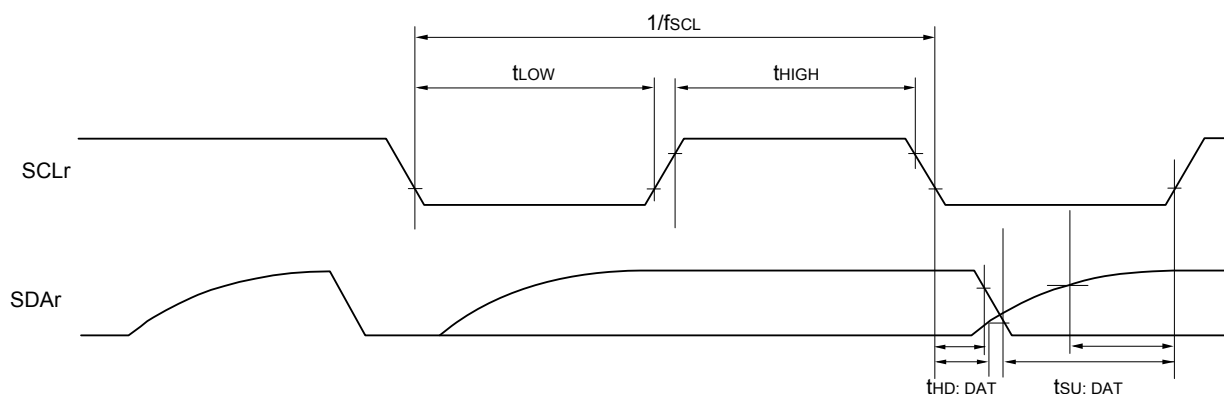
3.4 AC Characteristics

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq \text{EVDD0} = \text{EVDD1} \leq \text{VDD} \leq 5.5\text{ V}$, $\text{VSS} = \text{EVSS0} = \text{EVSS1} = 0\text{ V}$)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T _{CY}	Main system clock (f _{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem clock (f _{SUB}) operation		2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
				2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	f _{EX}	2.7 V ≤ V _{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V _{DD} ≤ 2.7 V			1.0		16.0	MHz
	f _{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t _{EXH} ,	2.7 V ≤ V _{DD} ≤ 5.5 V			24			ns
	t _{EXL}	2.4 V ≤ V _{DD} ≤ 2.7 V			30			ns
	t _{EXHS} , t _{EXLS}				13.7			μs
Ti00 to Ti03, Ti10 to Ti13 input high-level width, low-level width	t _{TIH} , t _{TIL}				1/f _{MCK} + 10 Note			ns
Timer RJ input cycle	f _C	TRJIO		2.7 V ≤ EV _{DD0} ≤ 5.5 V	100			ns
				2.4 V ≤ EV _{DD0} < 2.7 V	300			ns
Timer RJ input high-level width, low-level width	t _{TJIH} , t _{TJIL}	TRJIO		2.7 V ≤ EV _{DD0} ≤ 5.5 V	40			ns
				2.4 V ≤ EV _{DD0} < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when $\text{EVDD0} < \text{VDD}$
 $2.4\text{ V} \leq \text{EVDD0} < 2.7\text{ V}$: MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

Simplified I²C mode connection diagram (during communication at same potential)**Simplified I²C mode serial transfer timing (during communication at same potential)**

Remark 1. $R_b[\Omega]$: Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance

Remark 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 3 to 5, 14),
h: POM number (h = 0, 1, 3 to 5, 7, 14)

Remark 3. f_{MCK} : Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1),
n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

(TA = -40 to +105°C, 2.4 V ≤ EVDD0 = EVDD1 ≤ VDD ≤ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCKp cycle time Note 1	tkCY2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	24 MHz < fMCK	28/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	24/fMCK	ns
			8 MHz < fMCK ≤ 20 MHz	20/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK	ns
			fMCK ≤ 4 MHz	12/fMCK	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	24 MHz < fMCK	40/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	32/fMCK	ns
			16 MHz < fMCK ≤ 20 MHz	28/fMCK	ns
			8 MHz < fMCK ≤ 16 MHz	24/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	16/fMCK	ns
			fMCK ≤ 4 MHz	12/fMCK	ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	24 MHz < fMCK	96/fMCK	ns
			20 MHz < fMCK ≤ 24 MHz	72/fMCK	ns
			16 MHz < fMCK ≤ 20 MHz	64/fMCK	ns
			8 MHz < fMCK ≤ 16 MHz	52/fMCK	ns
			4 MHz < fMCK ≤ 8 MHz	32/fMCK	ns
			fMCK ≤ 4 MHz	20/fMCK	ns
SCKp high-/low-level width	tkH2, tkL2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	tkCY2/2 - 24		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	tkCY2/2 - 36		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	tkCY2/2 - 100		ns
Slp setup time (to SCKp↑) Note 2	tsIK2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V	1/fMCK + 40		ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V	1/fMCK + 40		ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V	1/fMCK + 60		ns
Slp hold time (from SCKp↑) Note 3	tsIS2		1/fMCK + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tkSO2	4.0 V ≤ EVDD0 ≤ 5.5 V, 2.7 V ≤ Vb ≤ 4.0 V, Cb = 30 pF, Rb = 1.4 kΩ		2/fMCK + 240	ns
		2.7 V ≤ EVDD0 < 4.0 V, 2.3 V ≤ Vb ≤ 2.7 V, Cb = 30 pF, Rb = 2.7 kΩ		2/fMCK + 428	ns
		2.4 V ≤ EVDD0 < 3.3 V, 1.6 V ≤ Vb ≤ 2.0 V, Cb = 30 pF, Rv = 5.5 kΩ		2/fMCK + 1146	ns

(Notes, Caution, and Remarks are listed on the next page.)

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

Reference Voltage	Reference voltage (+) = AV_{REFP} Reference voltage (-) = AV_{REFM}	Reference voltage (+) = V_{DD} Reference voltage (-) = V_{SS}	Reference voltage (+) = V_{BGR} Reference voltage (-) = AV_{REFM}
Input channel			
ANI0 to ANI14	Refer to 3.6.1 (1).	Refer to 3.6.1 (3).	Refer to 3.6.1 (4).
ANI16 to ANI20	Refer to 3.6.1 (2).		
Internal reference voltage Temperature sensor output voltage	Refer to 3.6.1 (1).		—

(1) When reference voltage (+) = $AV_{REFP}/ANI0$ ($ADREFP1 = 0$, $ADREFP0 = 1$), reference voltage (-) = $AV_{REFM}/ANI1$ ($ADREFM = 1$), target pin: ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

($T_A = -40$ to $+105^\circ\text{C}$, $2.4\text{ V} \leq AV_{REFP} \leq V_{DD} \leq 5.5\text{ V}$, $V_{SS} = 0\text{ V}$, Reference voltage (+) = AV_{REFP} ,

Reference voltage (-) = $AV_{REFM} = 0\text{ V}$)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution	RES		8		10	bit
Overall error Note 1	AINL	10-bit resolution $AV_{REFP} = V_{DD}$ Note 3	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$	1.2	± 3.5	LSB
Conversion time	t_{CONV}	10-bit resolution Target pin: ANI2 to ANI14	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.125	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.1875	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
		10-bit resolution Target pin: Internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$3.6\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	2.375	39	μs
			$2.7\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	3.5625	39	μs
			$2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$	17	39	μs
Zero-scale error Notes 1, 2	EZS	10-bit resolution $AV_{REFP} = V_{DD}$ Note 3	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.25	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution $AV_{REFP} = V_{DD}$ Note 3	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 0.25	%FSR
Integral linearity error Note 1	ILE	10-bit resolution $AV_{REFP} = V_{DD}$ Note 3	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 2.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution $AV_{REFP} = V_{DD}$ Note 3	$2.4\text{ V} \leq AV_{REFP} \leq 5.5\text{ V}$		± 1.5	LSB
Analog input voltage	V_{AIN}	ANI2 to ANI14	0		AV_{REFP}	V
		Internal reference voltage output ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)	V_{BGR} Note 4			V
		Temperature sensor output voltage ($2.4\text{ V} \leq V_{DD} \leq 5.5\text{ V}$, HS (high-speed main) mode)	V_{TMPS25} Note 4			V

Note 1. Excludes quantization error ($\pm 1/2$ LSB).

Note 2. This value is indicated as a ratio (%FSR) to the full-scale value.

Note 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

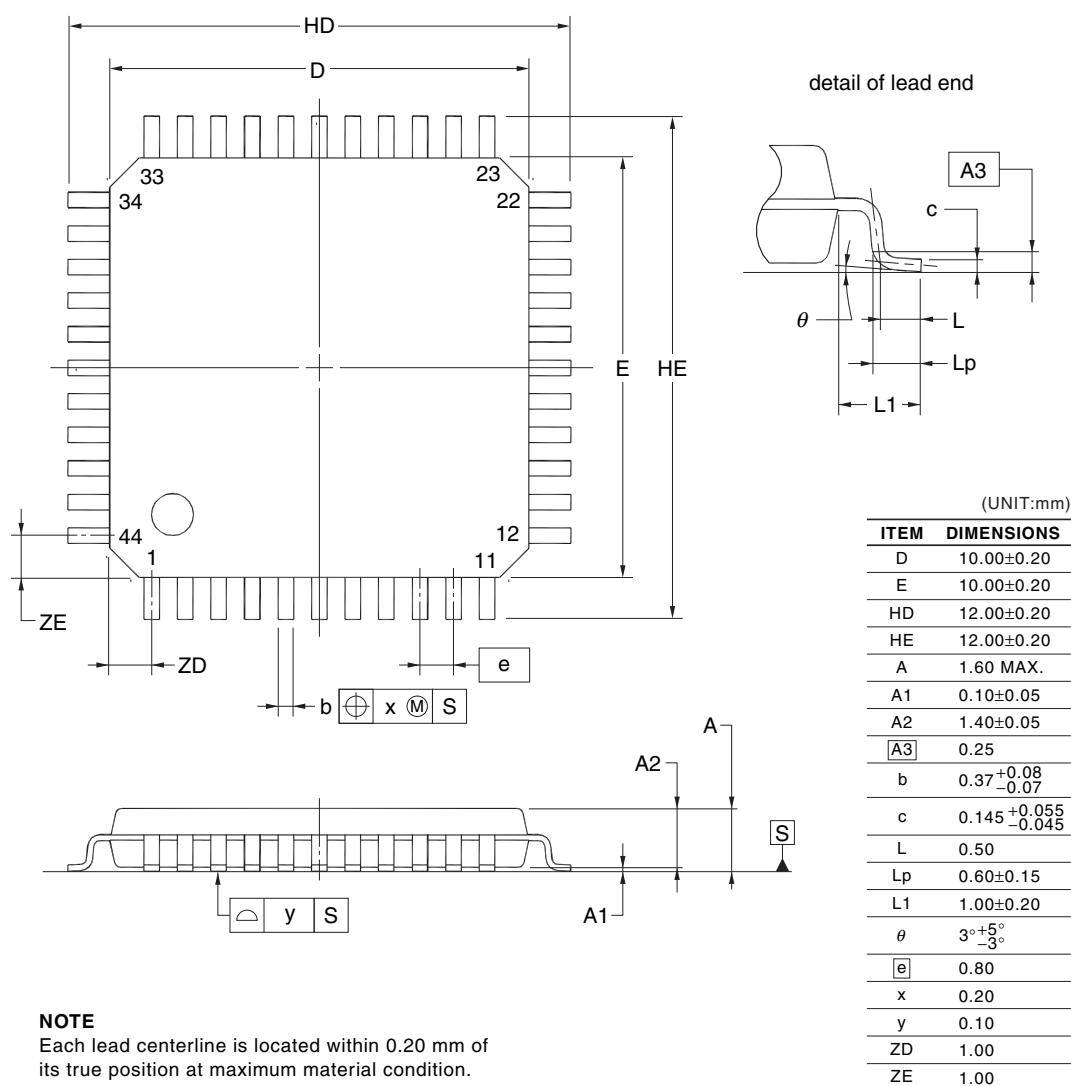
Overall error: Add ± 1.0 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.
 Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when $AV_{REFP} = V_{DD}$.
 Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when $AV_{REFP} = V_{DD}$.

Note 4. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

4.5 44-pin products

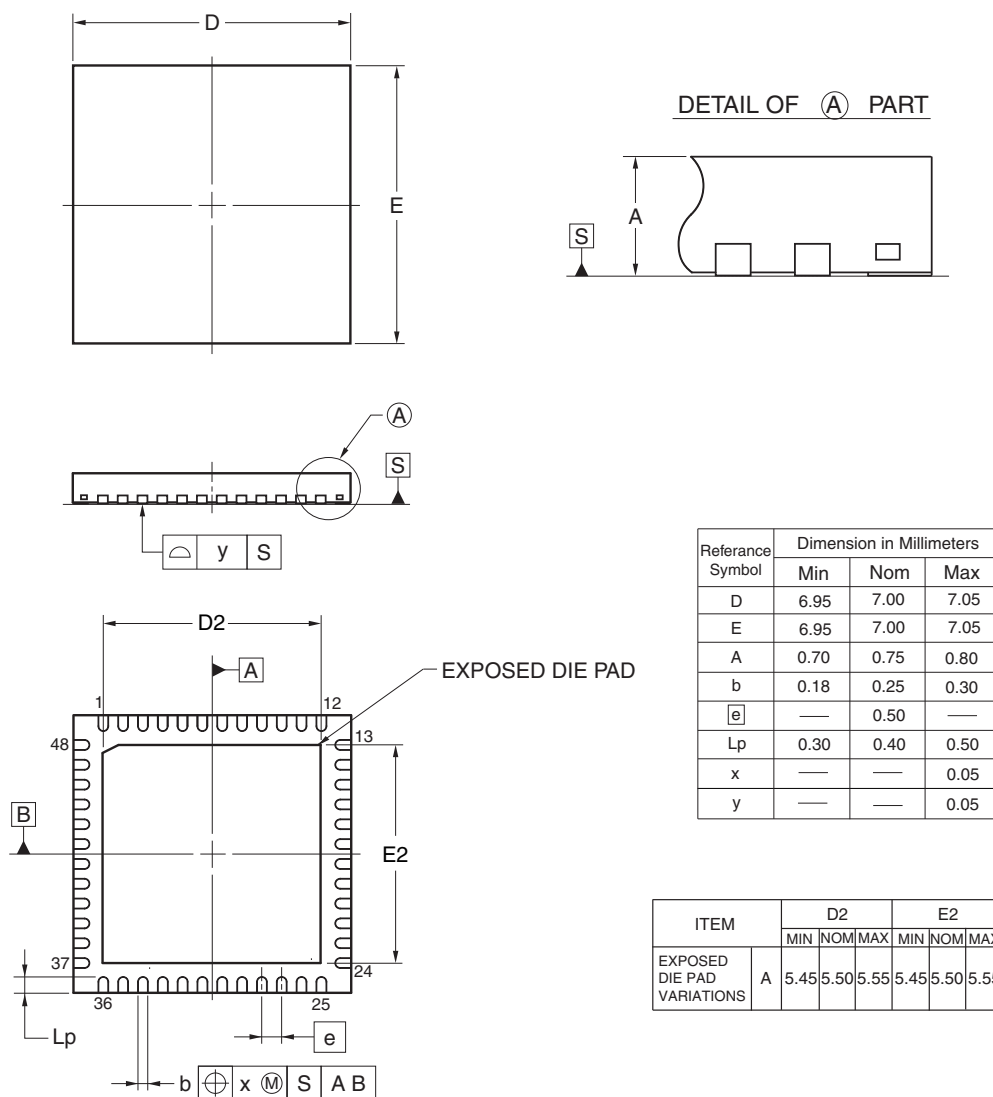
R5F104FAAFP, R5F104FCAFP, R5F104FDAFP, R5F104FEAFP, R5F104FFAFP, R5F104FGAFP,
 R5F104FHAFP, R5F104FJAFP
 R5F104FADFP, R5F104FCDFP, R5F104FDDFP, R5F104FEDFP, R5F104FFDFP, R5F104FGDFP,
 R5F104FHDFP, R5F104FJDFP
 R5F104FAGFP, R5F104FCGFP, R5F104FDGFP, R5F104FEGFP, R5F104FFGFP, R5F104FGGFP,
 R5F104FHGFP, R5F104FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



R5F104GAANA, R5F104GCANA, R5F104GDANA, R5F104GEANA, R5F104GFANA, R5F104GGANA,
 R5F104GHANA, R5F104GJANA
 R5F104GADNA, R5F104GCDNA, R5F104GDDNA, R5F104GEDNA, R5F104GFDNA, R5F104GGDNA,
 R5F104GHDNA, R5F104GJDNA
 R5F104GAGNA, R5F104GCGNA, R5F104GDGNA, R5F104GEGNA, R5F104GFGNA, R5F104GGGNA,
 R5F104GHGNA, R5F104GJGNA
 R5F104GKANA, R5F104GLANA
 R5F104GKGNA, R5F104GLGNA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-5	0.13



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